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THE RADIATION DESIGN HANDBOOK

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ABSTRACT

This handbook addresses the engineering problem of radiation effects in spacecraft and some of its management aspects. Summary graphs, tables and flow charts are compiled from a wide range of sources. The environment, the penetration and the effects of the space radiation environment are detailed. Assessment methods are also discussed.

The text and charts are to help spacecraft and instrument designers to gauge the significance of the space radiation problem from the project point of view, to communicate this problem to management and to implement engineering solutions.

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